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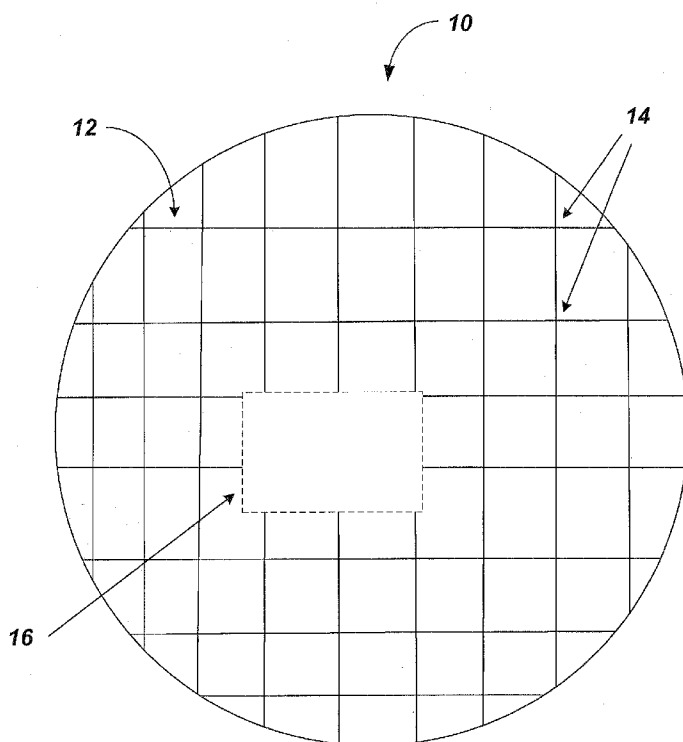


FIG. 1

(57) Abstract: A chemical mechanical polishing pad. The pad includes a surface and a polymer matrix capable of transmitting at least a portion of incident radiation. In addition, at least one embedded structure in the polymer matrix, including a portion of the pad where the embedded structure is not present, and a window integral to the pad defined by the portion of the pad where the embedded structure is not present.

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CHEMICAL-MECHANICAL PLANARIZATION PAD HAVING END POINT DETECTION WINDOW

CROSS REFERENCE TO RELATED APPLICATIONS

5 The present application claims the benefit of the filing date of U.S. Provisional Application Ser. No. 60/991,513, filed November 30, 2007, the teachings of which are incorporated herein by reference.

FIELD OF THE INVENTION

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The present invention relates to a polishing pad including an end point detection window that may be useful in chemical-mechanical planarization (CMP) of semiconductor wafers. The pads may include grooves as well as a grid network embedded in a continuous polymer matrix.

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BACKGROUND

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Semiconductor devices are formed from a flat, thin wafer of a semiconductor material, such as silicon. As the devices and layers of interconnecting circuits are deposited on the wafer, each layer must be polished to achieve a sufficiently flat surface with minimal defects before the next layer can be deposited. A variety of chemical, electrochemical, and chemical mechanical polishing techniques are employed to polish the wafers.

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In chemical mechanical polishing (CMP), a polishing pad made of polymer material, such as a polyurethane, may be used in conjunction with a slurry to polish the wafers. The slurry comprises abrasive particles, such as aluminum oxide, cerium oxide, or silica particles, dispersed in an aqueous medium. The abrasive particles generally range in size from 20 to 200 nanometers (nm). Other agents, such as surface acting agents, oxidizing agents, or pH regulators, are typically present in the slurry. The pad may also be textured, such as with grooves or perforations, to aid in the distribution of the slurry across the pad and wafer and removal of the slurry and by products therefrom.

For example, in U.S. Patent No. 6,656,018, whose teachings are incorporated herein by reference, a pad for polishing a substrate in the presence of a slurry is disclosed, where the slurry may contain abrasive particles and a dispersive agent. The pad itself may include a work surface and a backing surface. The pad may be formed from a two-component system,
5 a first component comprising a soluble component, a second component comprising a polymer matrix component, where the soluble component is distributed throughout at least an upper portion of the working structure and the soluble component may include fibrous materials soluble in the slurry to form a void structure in the work surface.

It is useful to end the CMP process when the desired amount of material has been
10 removed from the surface of the substrate. In some systems, the CMP process is continually monitored throughout in order to determine when the desired amount of material has been removed from the surface of the substrate, without stopping the process. This is typically done by in-situ optical end-point detection. In-situ optical end-point detection involves projecting optical (or some other) light through an aperture or a window in the polishing pad
15 from the platen side so that the optical light is reflected off the polished surface of the substrate and is collected by a detector to monitor the progress of planarization of the wafer surface.

SUMMARY

20 In a first aspect, the present disclosure relates to a chemical mechanical polishing pad. The pad may include a surface and a polymer matrix capable of transmitting at least a portion of incident radiation. In addition, the pad may include at least one embedded structure in the polymer matrix, including a portion of the pad where the embedded structure is not present, and a window integral to the pad defined by the portion of the pad where the
25 embedded structure is not present.

In another aspect, the present disclosure relates to a method. The method may include providing a mold having a first half and a second half and a recess defined in the first half, placing in the mold a fibrous structure to be embedded in a polymer matrix, placing in the mold a polymer matrix or a polymer matrix precursor for forming a polymer matrix, and
30 closing the mold and applying heat and pressure to the polymer matrix or precursor for forming the polymer matrix. The method may also include solidifying the polymer matrix or

the precursor for forming the polymer matrix and forming a pad, wherein the fibrous structure embedded in the polymer matrix includes a portion of the pad where the fibrous structure is not present, defining a window integral to the pad wherein said fibrous structure is not present.

5 In a further aspect, the present disclosure relates to a method of polishing a surface. The method may include providing a substrate for polishing having a surface, providing an aqueous slurry on at least a portion of the surface of the substrate, and providing a pad including a surface, wherein the pad comprises a polymer matrix capable of transmitting at least a portion of incident radiation. The pad may include at least one embedded structure in
10 the polymer matrix, including a portion of the pad where the embedded structure is not present; and a window integral to the pad defined by the portion of the pad where the embedded structure is not present. In addition, the method may include polishing the surface of the substrate by the interaction of the substrate, the aqueous slurry and the pad.

DETAILED DESCRIPTION

15 One example of a polishing pad herein is illustrated in **FIG. 1**. As shown, the pad **10** may include an embedded structure **12**, discussed more fully below, which structure may define a plurality of intersection locations **14**, dispersed in a pad polymer matrix. However, the structure may be provided such that it includes one or more window regions **16** where the
20 embedded structure is not present.

The polymer matrix may be selected from a polymer resin that is capable of providing optical end point detection via use of a laser or some other light through the window **16** that is then reflected off of the polished surface of a substrate. Thus, the polymer matrix may be capable of transmitting at least a portion of incident radiation, including optical radiation.
25 Incident radiation may be understood as radiation, such as light, which impinges on the surface of the polymer matrix. At least 1 % or more of the radiation may be transmitted through a portion of the polymer matrix, such as through the thickness of the pad, including all values and increments in the range of 1 % to 99 %.

The window **16** may assume any desired geometry, such as round, oval, square,
30 rectangular, polyhedral, etc. In addition, as illustrated in **FIG. 2**, the embedded structure may

also amount to a non-interconnecting type pattern **18** which again includes a window region **16**. The embedded structure may also amount to a random type pattern.

The embedded structure itself may be composed of fibers, more specifically in the form of a nonwoven, woven, and/or knitted fabric type configuration. Such network of fibers
5 may enhance certain features of the pad. Such features may include, e.g., pad surface hardness and/or bulk modulus and/or rigidity. In addition, the fiber network may be configured so that it enhances such features differently, as may be desired for a given polishing pad product. Therefore, the pads herein may be configured as desired to provide better global uniformity and local planarity of the polished semiconductor wafer, as well as
10 window end-point detection capability. Expanding upon the above, other available materials for embedded structure may include open-cell polymeric foams and sponges, polymeric filters (e.g. filter paper and fibrous filters) grids and screens. The embedded structure may therefore have a defined two dimensional or three-dimensional pattern. The embedded structure therefore may be understood as any material dispersed in the pad with a selective
15 region where the structure is not present, which region defines a window location for end point detection of a given polishing operation.

As may now be appreciated, by incorporating an embedded structure into the polymer matrix that is used to form the pad, such that a window is provided that may be considered integral to the pad structure (i.e. the pad being of unitary construction), one may avoid some
20 of the problems associated with separately installing a window into the pad after it has been formed. For example, when manufacturing a pad to include a window, one may typically cut an opening in the pad and install a transparent section of material. However, this may then lead to leakage of the slurry due to improper installation around the edges of the window insert.

The polymeric substances, as well as the embedded structure, may be sourced from, but not be limited to, a variety of specific polymeric resins. For example, the polymeric resins may include polyvinylalcohol, polyacrylate, polyacrylic acids, hydroxyethylcellulose, hydroxymethylcellulose, methylcellulose, carboxymethylcellulose, polyethylene glycol, starch, maleic acid copolymer, polysaccharide, pectin, alginate, polyurethane, polyethylene
25 oxide, polycarbonate, polyester, polyamide, polypropylene, polyacrylamide, polyamide, as
30 well as any copolymers and derivatives of the above resins.

The pads herein may optionally be grooved on at least one surface. Such grooving may be applied to the window based pads noted above, and or even to pads that do not include such a window configuration. Accordingly, the pads may include a variety of groove patterns, such as concentric, spiral, log positive and negative (counterclockwise and clockwise) and or combinations thereof. The groove dimensions may include a depth of 0.10 microns and above, a width of 0.10 microns and above, and a pitch (distance from center to center of adjacent grooves) of 0.10 microns and above. For example, the pads herein may contain groove depths of 50 to 5000 microns, widths of 50 to 5000 microns and a pitch of 50 to 2600 microns. For all of these values, it should be understood that the present disclosure include all values and increments within the particular range recited.

In particular, the pitch of the grooves herein may have a value of 1500 microns to 2250 microns (59 mils to 89 mils), including all values and increments therein. In such regard, reference is made to **FIG. 3**, which illustrates the removal rate (RR) in Angstroms/minute for the RR of SX1122-21, having a groove width of 508 microns, a groove depth of 762 microns, and a pitch of 2159 microns. As can be seen, such pad characteristics provided a relatively higher removal rate as compared to the RR of IC-1010, which has a groove width of 508 microns, a groove depth of 762 microns, and a pitch of 2286 microns. In addition, it may be noted that SX1122-21 maintained a non-uniformity (NU) of less than 6.0%, which is considered acceptable for pad polishing. Reference to the parameter NU is reference to a variation in thickness of the polished wafer.

Attention is next directed to **FIG. 4** which provides further comparative data regarding the SX1122 pad, noted above (two pad samples) versus IC-1010 available from Rohm & Haas. The parameters evaluated were "Recess 0.5" which is reference to the distance between the top of the insulating region on the pad to the adjoining 0.5 micron conductive trace. As can be seen, IC1010 indicated this vertical measurement to be 400 Angstroms, whereas the SX1122 indicated a vertical measurement of between 150-200 Angstroms. The parameter of "Erosion" is also shown, which may be understood as the undesirable excess removal of the insulation layer. As can be seen, IC1010 had a vertical measurement of about 175 Angstroms, whereas the SX1122 indicated vertical measurements of about 100 Angstroms (pad 1) or about 150 Angstroms (pad 2). The parameter of EOE or "Edge on Erosion" indicates a horizontal measurement reflecting a non-effective polishing

area located on the perimeter of a given pad. As can be seen, IC1010 had an EOE of about 425 Angstroms, whereas the SX122 indicated values of about 200-225 Angstroms.

As alluded to above, the embedded structure portion of the pad herein may be understood as incorporating a three-dimensional structure with a given pad, one example of which is shown in **FIG. 5**. As can be seen, it may include interconnecting polymer elements **20** along with a plurality of junction locations **22**. Within the three-dimensional structure (i.e. the interstices) may be a particular polymeric binder material **24** (i.e., the polymer matrix) which, when combined with the three-dimensional interconnecting polymer elements **20**, provide the polishing pad substrate. In addition, although the network is shown with a relative square or rectangular geometry, it may be appreciated that it may include other types of structures, including, but not limited to oval, round, polyhedral, etc.

In addition, a further aspect of this invention is the use of multiple three-dimensional embedded structural networks along with an integrally formed window which network may affect different physical and chemical property domains within the same pad. Accordingly, one may vary the chemical (polymeric) composition noted above for the embedded structural elements **20** and/or physical features of such elements. Such physical features may include the spacing of the elements **20**, and or the overall shape of the embedded structural elements, as explained more fully below.

It is worth noting that advanced semiconductor technology requires packing a large number of smaller devices on the semiconductor wafer. Greater device density in turn requires greater degrees of local planarity and global uniformity over the wafer for depth of focus reasons in photo lithography. The three-dimensional structural network and window configuration in the present invention may therefore enhance the mechanical and dimensional stability of the CMP pad over conventional, non-network based CMP pad structures. The three-dimensional embedded structure herein with an integrally formed window may also better withstand the compressive and viscous shear stress of the polishing action, resulting in the desired degree of local planarity and global uniformity as well as low wafer scratching defects, as the surface deformation of the pad is reduced.

As alluded to above, the actual three-dimensional embedded structure within the pad can also be customized for a particular CMP application by varying the type of polymeric materials, the dimensions of the interconnecting and embedded elements, and the size and shape of the elements. In addition, various chemical agents including, but not limited to,

surfactants, stabilizers, inhibitors, pH buffers, anti-coagulants, chelating agents, accelerators and dispersants may be added to the surface or bulk of the pad, so that they can be released in a controlled or uncontrolled manner into an abrasive slurry or polishing fluid to enhance CMP performance and stability.

5 One exemplary embodiment of the present invention comprises a polyurethane substance dispersed and partially or completely filling the interstices of a three-dimensional network made up of water-soluble (e.g. polyacrylate) embedded and interconnecting and embedded structural elements. The interconnecting elements within the pad and dispersed in the polyurethane may have a cylindrical shape with diameters from below 1 micron (e.g. 0.1
10 microns) to about 1000 microns, and what may be described as a horizontal length between adjacent interconnecting junctures ranging from 0.1 microns and higher (e.g. junctures with a horizontal length therebetween ranging from 0.1 microns to 20 cm, including all values and increments therein). This length between interconnecting junctures is show as item "A" in **FIG. 5**. In addition, what may be described as the vertical distance between interconnecting
15 junctures is shown as item "B" in **FIG. 5**, and this may also vary as desired from 0.1 microns and higher (e.g., junctures having a vertical length therebetween ranging from 0.1 microns to 20 cm, including all values and increments therein). Finally, in what may described as a depth distance between junctures is shown as item "C" in **FIG. 5**, and again, this may also vary as desired from 0.1 microns and higher (e.g. junctures having a depth distance
20 therebetween ranging from 0.1 microns to 20 cm, including all values and increments therein).

The three-dimensional embedded structure itself may be in the form of a thin square or circular slab with thickness in the range of 10 to 6000 mils and preferably between 60 to 130 mils, and an area between 20 to 4000 square inches and preferably between 100 to 1600
25 square inches, including all values and increments therein. A urethane pre-polymer mixed with a curing agent may be used to fill the interstices of the embedded structure, and the composite is then cured in an oven to complete the curing reaction of the urethane pre-polymer. Typical curing temperature ranges from room temperature to 800 deg F., and typical curing time ranges from as little as under an hour to over 24 hours. The resulting composite is
30 then converted into a CMP pad using conventional pad converting processes such as buffing, skiving, laminating, grooving and perforating.

The embedded structure may also be available in the form of a cylinder or rectangular block in the above mentioned embodiment. It follows, then, that the composite comprising the embedded structure herein filled with urethane pre-polymer mixed with curing agent may also be cured in the form of a cylinder or rectangular block. In this case, the cured composite
5 cylinder or block may first be skived to yield individual pads before converting.

Another embodiment of the present invention comprises two or more embedded structures having different thicknesses, the embedded structures further differentiated from each other by the types of polymeric material contained therein. For example, one portion of the pad included a first embedded structure may have a thickness of 1-20 centimeters and a
10 second portion of the pad including a second embedded structure may have a thickness of 1-20 cm, each including all values and increments therein. The embedded structures within the same CMP pad then may define different pad domains having different physical and chemical properties, due to a selected difference in the chemical or physical properties of the embedded structures. For example, the first embedded structure may be selected from a first
15 polymer and the second embedded structure may be selected from a second polymer, where the polymers differ in chemical repeating unit structure. A difference in chemical repeating unit composition may be understood as a difference in at least one element of the repeating unit, as between the two polymers selected, or a difference in the number of elements in the repeating units. For example, the first and second polymer may be selected from polymers
20 such as polyesters, nylons, cellulotics, polyolefins, polyacrylates, modified acrylic fibers such as polyacrylonitrile based fibers, polyurethanes, etc.

One example would include a CMP pad having a first 20 mils thick region comprising embedded structure of soluble polyacrylate fibers in relatively small cylindrical form 10 microns diameter and 50 to 150 microns apart from each other that is stacked onto a second
25 embedded structure comprising polyester fibers in the same cylindrical form and having the same dimensions as for the said first polyacrylate network of fibers. A urethane pre-polymer mixed with a curing agent may then be used to fill the interstices of the stacked fiber networks, and the entire composite is cured as mentioned above. The resulting composite is then converted into a CMP pad using conventional pad converting processes such as buffing,
30 skiving, laminating, grooving and perforating. The CMP pad made in this manner has therefore two distinctly different but attached structural layers stacked on one another. In CMP, the layer comprising the soluble polyacrylate fibrous elements may be used as the

polishing layer. The soluble polyacrylate elements may dissolve in the aqueous slurry containing the abrasive particles, leaving void spaces on and under the surface of the pad creating micron sized channels and tunnels for even distribution of the the slurry throughout the pad. The layer containing the relatively insoluble polyester elements, on the other hand,
5 may be employed as the supporting layer to maintain mechanical stability and bulk pad properties in CMP.

The aforementioned embodiments notwithstanding, it is recognized herein that one who is skilled in the art of CMP pad design, manufacture and application can readily appreciate the unexpected properties by the incorporation of the structural network into a
10 CMP pad, and can readily derive, based on the present invention, a multitude of pad designs using the same concept with various types of network materials, structure, and polymeric substances in the same pad to meet the requirements of particular CMP applications.

What is claimed is:

Claims

1. A chemical mechanical polishing pad, comprising:
a pad including a surface, comprising a polymer matrix capable of transmitting at least a portion of incident radiation;
5 at least one embedded structure in said polymer matrix, including a portion of said pad where said embedded structure is not present; and
a window integral to said pad defined by said portion of said pad where said embedded structure is not present.
2. The polishing pad of claim 1, wherein said embedded structure comprises one or a
10 plurality of fibers.
3. The polishing pad of claim 2 wherein said fibers have a diameter of 0.1 microns to 1000 microns.
4. The polishing pad of claim 1 wherein said embedded structure comprises fibers which include interconnecting junctures wherein said interconnecting junctures are spaced
15 between 0.1 microns to 20 cm.
5. The polishing pad of claim 4 wherein said interconnecting junctures are spaced in a length direction, a horizontal direction, and/or a vertical direction.
6. The polishing pad of claim 1 wherein said at least one embedded structure comprises a first polymer, and said pad further includes a second embedded structure comprising
20 a second polymer, wherein said first polymer and second polymer comprise different chemical repeating unit composition.
7. The polishing pad of claim 1, further comprising at least one groove defined in said surface.
8. The polishing pad of claim 7, wherein said at least one groove has a depth of 0.1
25 micron and above, a width of 0.1 micron and above, and wherein more than one groove is present a pitch of 0.1 micron and above.

9. The polishing pad of claim 1, wherein said at least one embedded structure includes a soluble material.
10. A method comprising:
- 5 providing a mold having a first half and a second half and a recess defined in said first half;
- placing in said mold a fibrous structure to be embedded in a polymer matrix;
- placing in said mold a polymer matrix or a polymer matrix precursor for forming a polymer matrix;
- 10 closing said mold and applying heat and pressure to said polymer matrix or precursor for forming said polymer matrix;
- solidifying said polymer matrix or said precursor for forming said polymer matrix and forming a pad;
- 15 wherein said fibrous structure embedded in said polymer matrix includes a portion of said pad where said fibrous structure is not present, defining a window integral to said pad wherein said fibrous structure is not present.
11. The method of claim 10, wherein said polymer matrix pre-cursor comprises a prepolymer and a curing agent.
12. The method of claim 10, wherein said method further comprises curing said pad.
13. The method of claim 10 wherein said fibers have a diameter of 0.1 microns to 1000
20 microns.
14. The method of claim 10 wherein said embedded structure comprises fibers which include interconnecting junctures wherein said interconnecting junctures are spaced between 0.1 microns to 20 cm.
15. The method of claim 14 wherein said interconnecting junctures are spaced in a length
25 direction, a horizontal direction, and/or a vertical direction.
16. The method of claim 10 wherein said at least one embedded structure comprises a first polymer, and said pad further includes a second embedded structure comprising a

second polymer, wherein said first polymer and second polymer comprise different chemical repeating unit composition.

17. The method of claim 10, further comprising at least one groove defined in said surface.

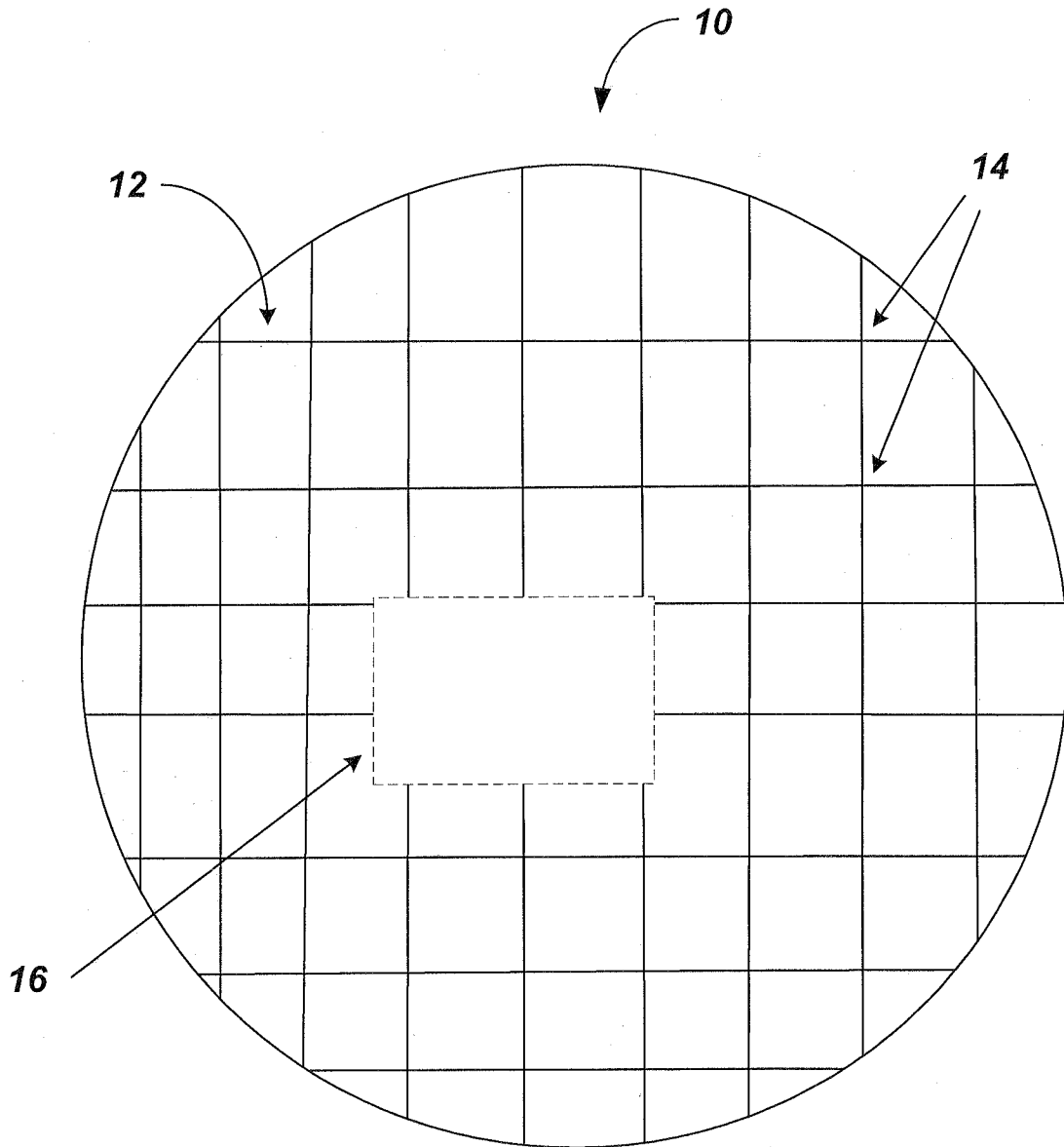
5 18. The method of claim 17, wherein said at least one groove has a depth of 0.1 micron and above, a width of 0.1 micron and above, and wherein more than one groove is present a pitch of 0.1 micron and above.

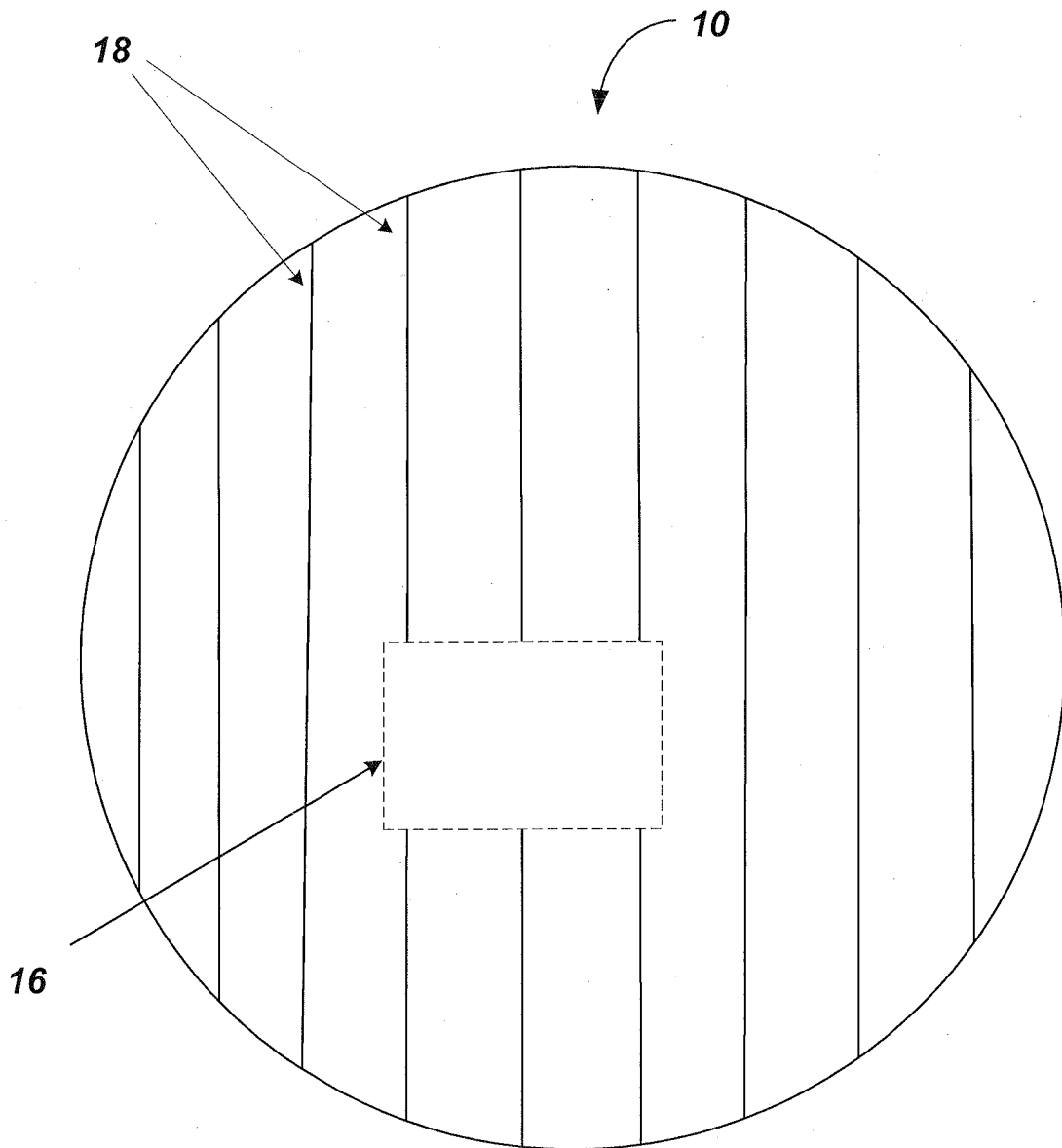
19. The method of claim 10, wherein said at least one embedded structure includes a soluble material.

10 20. A method of polishing a surface, comprising:
providing a substrate for polishing having a surface;
providing an aqueous slurry on at least a portion of said surface of said substrate;
providing a pad including a surface, comprising a polymer matrix capable of
15 transmitting at least a portion of incident radiation, said pad including at least one embedded structure in said polymer matrix, including a portion of said pad where said embedded structure is not present; and a window integral to said pad defined by said portion of said pad where said embedded structure is not present; and
polishing said surface by the interaction of said substrate, said aqueous slurry
20 and said pad.

21. The method of claim 20, further comprising providing radiation from an emitter and detecting at least a portion of said radiation reflected by said substrate by a sensor.

22. The method of claim 21, wherein said detected radiation indicates a polishing end point.

**FIG. 1**

**FIG. 2**

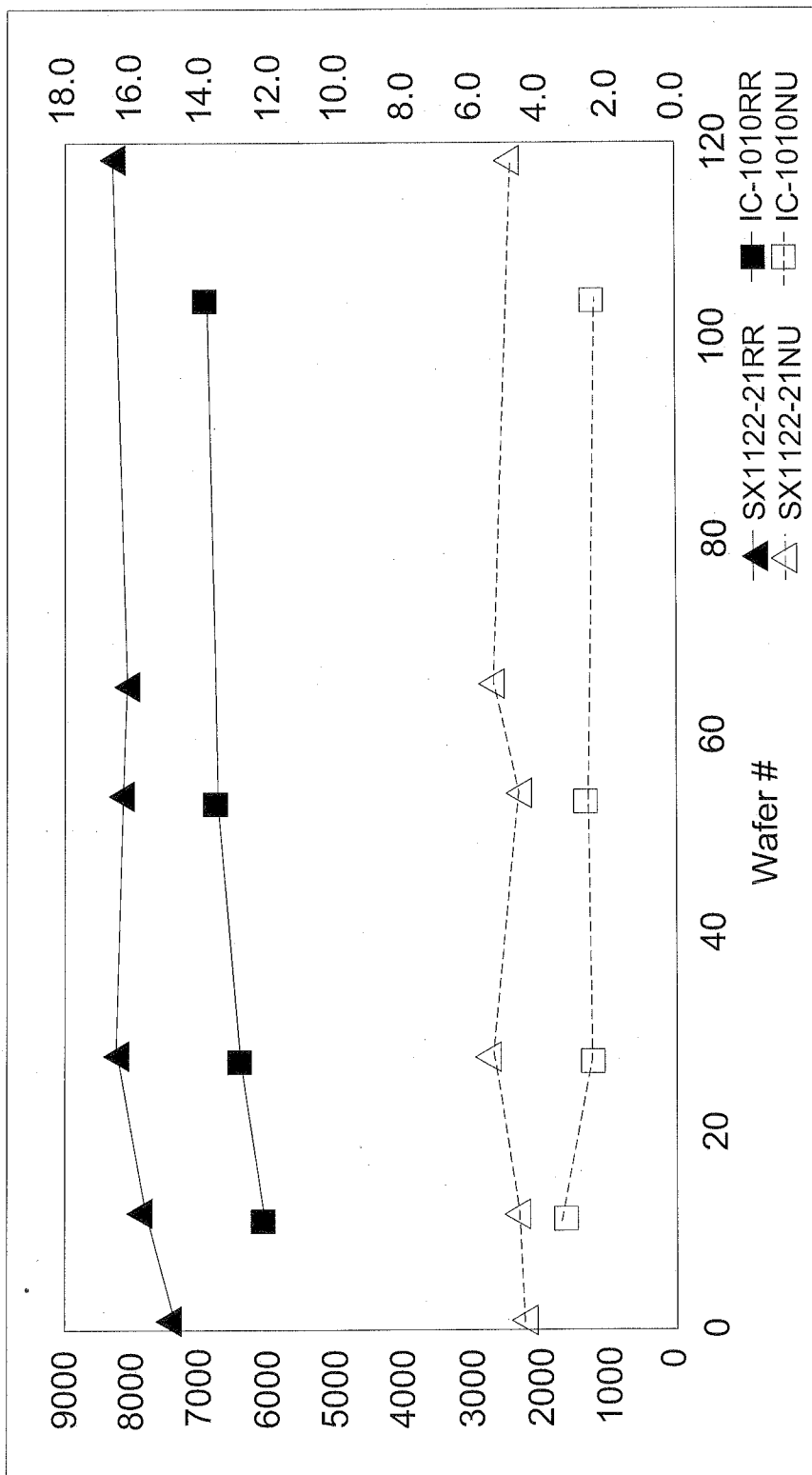


FIG. 3

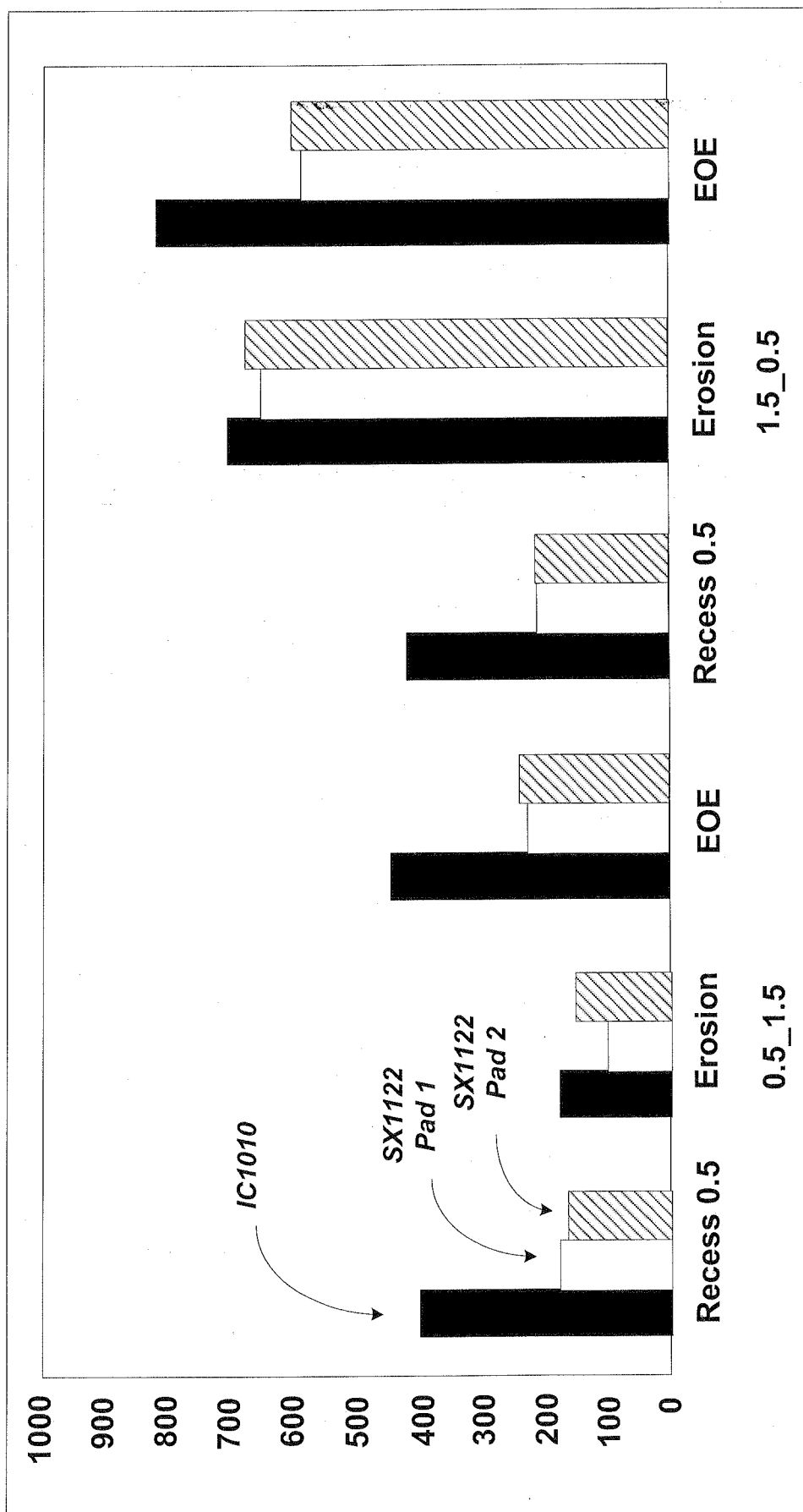


FIG. 4

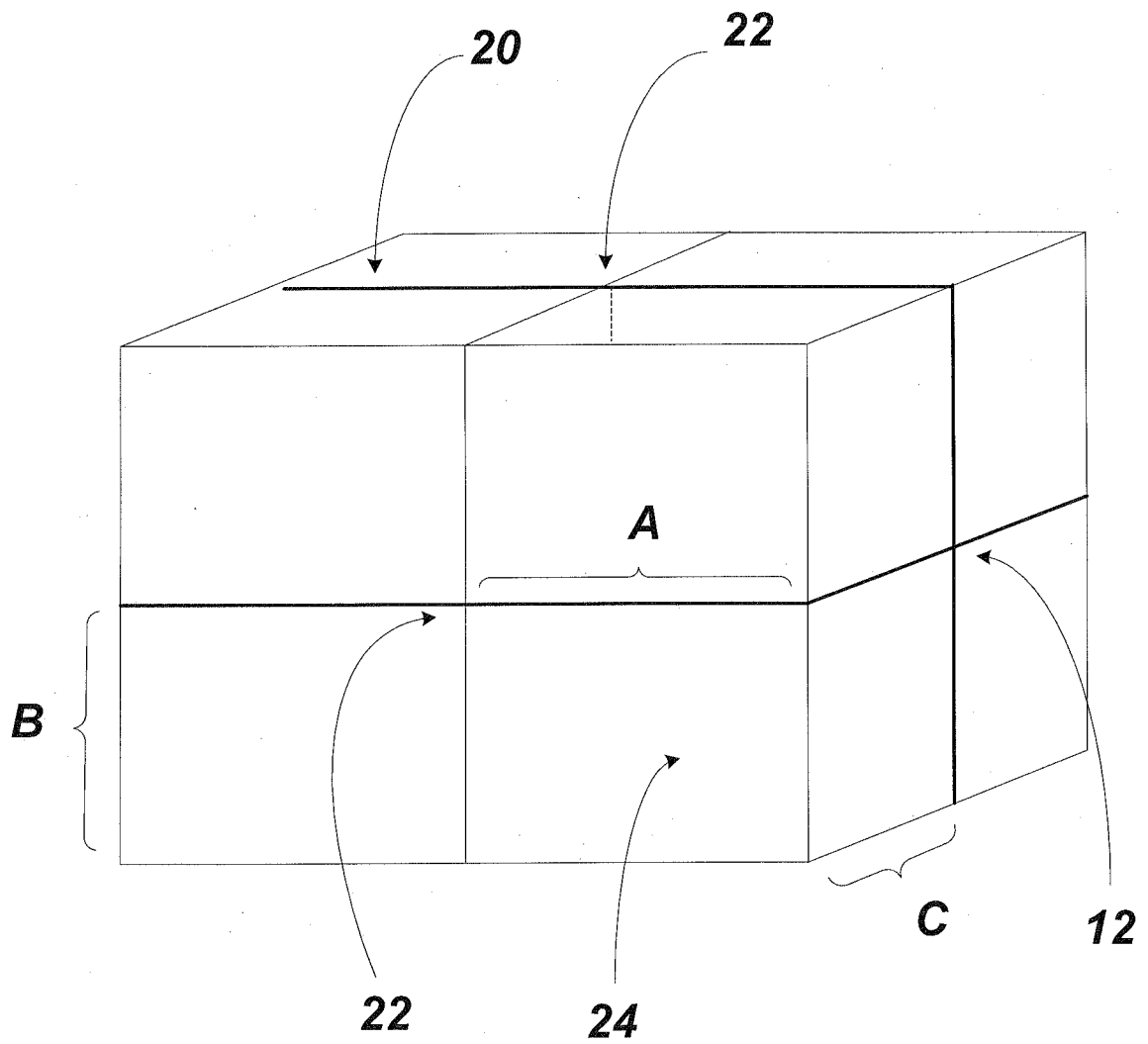


FIG. 5

INTERNATIONAL SEARCH REPORT

International application No.

PCT/US 08/71074

A. CLASSIFICATION OF SUBJECT MATTER

IPC(8) - B24B 5/00 (2008.04)

USPC - 451/287

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

IPC(8) - B24B 5/00 (2008.04)

USPC - 451/287

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched
USPC - 451/41,42,259,285,287

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

PubWEST; Google Scholar Database; Google Patents Database

(chemical, mechanical, polish, pad, polymer, matrix, radiation, fiber, micron, diameter, interconnecting, juncture, groove, depth, mold, curing, soluble, aqueous, slurry, sensor, endpoint)

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	US 2006/0276109 A1 (Roy, et al.) 7 Dec 2006 (07.12.2006) paragraphs 0015, 0018, 0025-0026, 0030, 0075, 0079, 0082-0083, 0108-0109, 0132, 0134, 0136, 0139, 0142, 0147-0148, 0159, 0170-0171, 0180-0181, 0196	1-22
A	US 6,621,584 B2 (Pecen, et al.) 16 Sep 2003 (16.09.2003)	1-22
A	US 2006/0166608 A1 (Chalmers, et al.) 27 Jul 2006 (27.07.2006)	1-22

☐

Further documents are listed in the continuation of Box C.

☐

* Special categories of cited documents:

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Date of the actual completion of the international search

11 Oct 2008 (11.10.2008)

Date of mailing of the international search report

22 OCT 2008

Name and mailing address of the ISA/US

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